

Table I (input conditions)

Spl- Sample, T_{sub} - Substrate Temperature ($^{\circ}\text{C}$), E_s - Surface energy (eV), E_{sch} -Schwoebel Barrier(eV), E_n - Incorporation Barrier(eV), E_d -Desorption Barrier (eV),

Sp I	Growth Steps	Orifice Area (cm^2)	Cell distance from substrate (cm)	Sticking Coeffici ent	T_{sub} ($^{\circ}\text{C}$)	E_s (eV)	E_{sch} (eV)	E_n (eV)	E_d (eV)
I	AlSb/GaSb/InAs/ AlSb/InAs/AlSb/In As/AlSb/InAs	0.002	15	1	800	2.0	0.1	0.1	3.0

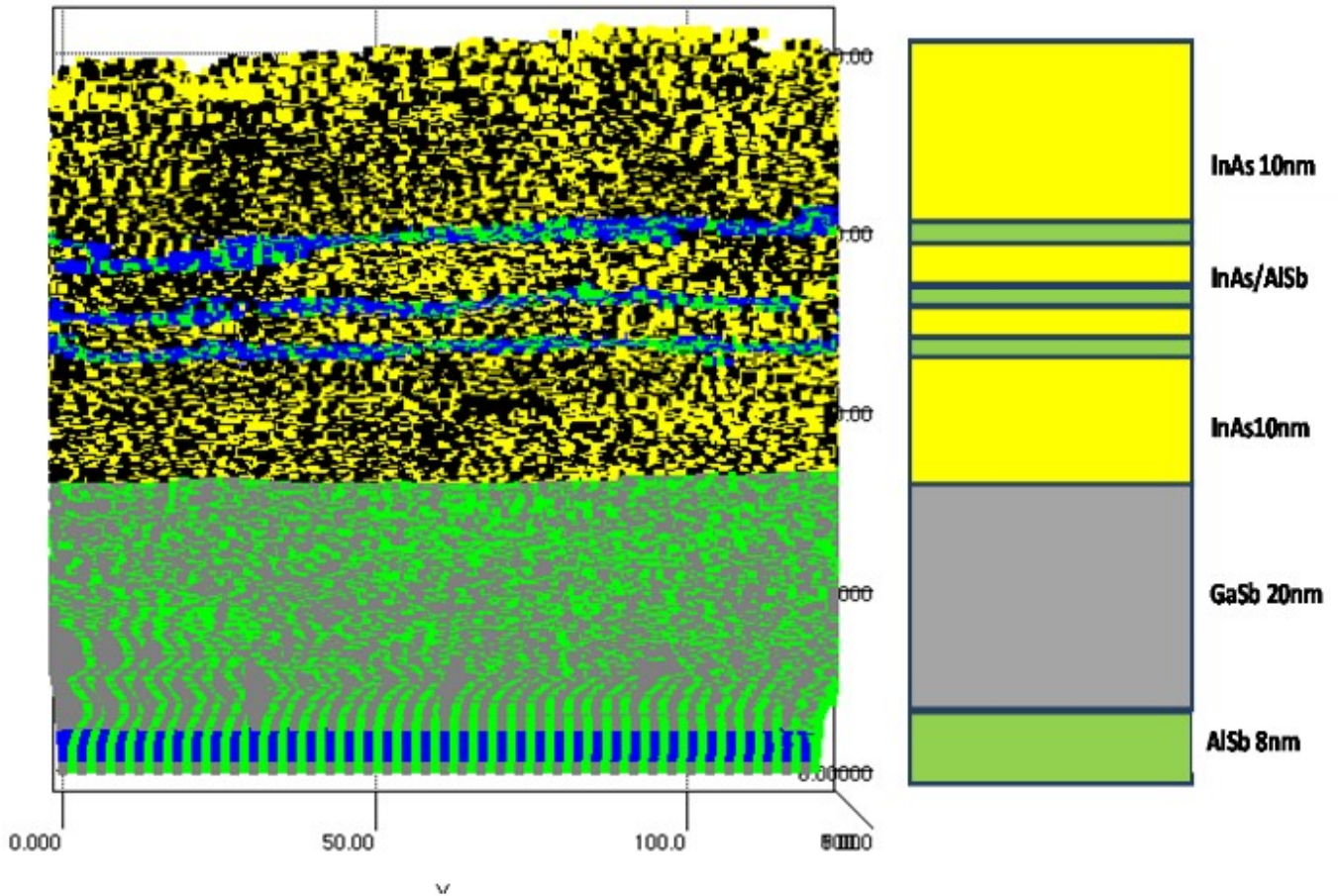


Fig.1a: Atomistic film layer-by-layer profile (Al-Blue, Ga-Gray, As—Black, In—Yellow and Sb--Green). For better visualization the schematic layers are shown.

Table II: Extracted Output Parameters

Deposited Materials	Lattice Parameters (Å)			Vacancy (per Å ⁻³)	Dislocation (per Å ⁻²)
	a (Å)	b (Å)	c (Å)		
AlSb	6.114	6.099	9.193	1.1×10^{-5}	0
GaSb	5.512	5.952	6.95	3.2×10^{-3}	1.63×10^{-3}
InAs	4.484	4.736	7.655	5.4×10^{-3}	1.65×10^{-3}
AlSb	4.194	4.191	7.81	8.8×10^{-3}	1.25×10^{-3}
InAs	4.286	5.564	7.253	9.3×10^{-3}	1.27×10^{-3}
AlSb	4.309	5.693	7.221	6.4×10^{-3}	9.64×10^{-4}
InAs	4.25	4.343	7.959	7.3×10^{-3}	1.07×10^{-3}
AlSb	4.201	4.312	7.63	6.1×10^{-3}	7.26×10^{-4}
InAs	4.018	4.236	7.827	7.2×10^{-3}	1.03×10^{-3}